

TOSHIBA

MG25Q1BS11

TOSHIBA GTR MODULE SILICON N CHANNEL IGBT

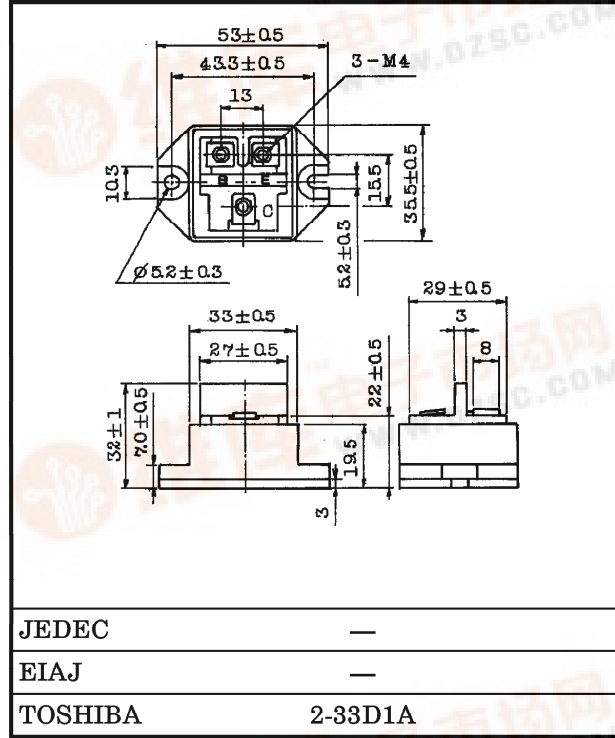
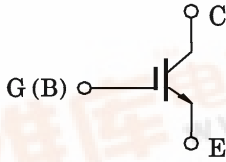
MG25Q1BS11

HIGH POWER SWITCHING APPLICATIONS.
MOTOR CONTROL APPLICATIONS.

Unit in mm

- High Input Impedance
- High Speed : $t_f = 1.0 \mu s$ (Max.)
- Low Saturation Voltage: $V_{CE(sat)} = 2.7V$ (Max.)
- Enhancement-Mode
- The Electrodes are Isolated from Case.

EQUIVALENT CIRCUIT



Weight : 90g

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Emitter Voltage	V_{CES}	1200	V
Gate-Emitter Voltage	V_{GES}	± 20	V
Collector Current	DC	I_C	25
	1ms	I_{CP}	50
Collector Power Dissipation (Tc = 25°C)	P_C	150	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-40~125	°C
Isolation Voltage	V_{Isol}	2500 (AC 1 Minute)	V
Screw Torque (Terminal / Mounting)	—	2 / 3	N · m

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Gate Leakage Current	I_{GES}	$V_{GE} = \pm 20V, V_{CE} = 0$	—	—	± 500	nA	
Collector Cut-off Current	I_{CES}	$V_{CE} = 1200V, V_{GE} = 0$	—	—	1.0	mA	
Collector-Emitter Voltage	V_{CES}	$I_C \leq 1mA, V_{GE} = 0$ Note 1	1200	—	—	V	
Gate-Emitter Cut-off Voltage	$V_{GE(OFF)}$	$I_C = 25mA, V_{CE} = 5V$	3.0	—	6.0	V	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 25A, V_{GE} = 15V$	—	2.3	2.7	V	
Input Capacitance	C_{ies}	$V_{CE} = 10V, V_{GE} = 0, f = 1MHz$	—	3000	—	pF	
Switching Time	Rise Time	t_r		—	0.3	0.6	μs
	Turn-on Time	t_{on}		—	0.4	0.8	
	Fall Time	t_f		—	0.6	1.0	
	Turn-off Time	t_{off}		—	1.2	1.8	
Thermal Resistance	$R_{th(j-c)}$	—	—	—	0.83	°C/W	

Note 1 : Do not apply the over rating voltage.

